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Authors: Jingnan Tong, Yimao Wan, Jie Cui, Sean Lim, Ning Song, Alison Lennon



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## ACCEPTED MANUSCRIPT

### Solution-processed Molybdenum Oxide for Hole-selective Contacts on Crystalline Silicon Solar Cells

Jingnan Tong \*<sup>†</sup>, Yimao Wan<sup>‡</sup>, Jie Cui<sup>‡</sup>, Sean Lim<sup>§</sup>, Ning Song<sup>†</sup>, Alison Lennon<sup>†</sup>

<sup>†</sup>School of Photovoltaic and Renewable Energy Engineering, UNSW Sydney, NSW, 2052, Australia
<sup>‡</sup>Research School of Engineering, The Australia National University (ANU), Canberra, Australia Capital Territory 0200, Australia
<sup>§</sup>Mark Wainwright Analytical Centre, UNSW Sydney, NSW, 2052, Australia

*KEYWORDS:* Hydrogen molybdenum bronzes; molybdenum oxide; silicon photovoltaics; hole-selective contact; surface passivation

Graphical Abstract:



Highlights:

- Hydrogen molybdenum bronze solution was used to form hole-selective contacting layers for c-Si solar cells.
- An ultra-thin interfacial silicon oxide layer was formed between spin-coated MoO<sub>x</sub> film and silicon substrate.
- Solution-processed MoO<sub>x</sub> films showed comparable contact resistivity and passivation quality on c-Si wafers to thermally-evaporated MoO<sub>x</sub>.

#### Abstract

Sub-stoichiometric molybdenum oxide (MoO<sub>x</sub>) films are commonly deposited on crystalline

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